

# General Purpose Transistor

## MBT2222ADW1, NSVBT2222ADW1 NPN Silicon

### Features

- Moisture Sensitivity Level: 1
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	40	Vdc
Collector-Base Voltage	$V_{CBO}$	75	Vdc
Emitter-Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current – Continuous	$I_C$	600	mAdc
Electrostatic Discharge	ESD	HBM Class 2 MM Class B	

### THERMAL CHARACTERISTICS

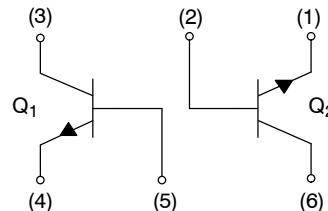
Characteristic	Symbol	Max	Unit
Total Package Dissipation (Note 1), $T_A = 25^\circ\text{C}$	$P_D$	150	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

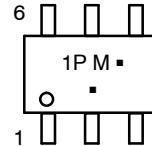
1. Device mounted on FR4 glass epoxy printed circuit board using the minimum recommended footprint.



SC-88/SC70-6/SOT-363  
CASE 419B  
STYLE 1



### MARKING DIAGRAM



1P = Specific Device Code

M = Date Code

■ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MBT2222ADW1T1G	SOT-363 (Pb-Free)	3000 / Tape & Reel
NSVBT2222ADW1T1G	SOT-363 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

# MBT2222ADW1, NSVBT2222ADW1

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	40	–	Vdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 μA, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	75	–	Vdc
Emitter-Base Breakdown Voltage, (I <sub>E</sub> = 10 μA, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	6.0	–	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 60 Vdc, V <sub>EB(off)</sub> = 3.0 Vdc)	I <sub>CEX</sub>	–	10	nA
Collector Cutoff Current (V <sub>CB</sub> = 60 Vdc, I <sub>E</sub> = 0, T <sub>A</sub> = 125°C)	I <sub>CBO</sub>	–	0.01 10	μA
Emitter Cutoff Current (V <sub>EB</sub> = 3.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	–	100	nA
Base Cutoff Current (V <sub>CE</sub> = 60 Vdc, V <sub>EB(off)</sub> = 3.0 Vdc)	I <sub>BL</sub>	–	20	nA

## ON CHARACTERISTICS

DC Current Gain (I <sub>C</sub> = 0.1 mA, V <sub>CE</sub> = 10 Vdc) (I <sub>C</sub> = 1.0 mA, V <sub>CE</sub> = 10 Vdc) (I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 10 Vdc) (I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 10 Vdc, T <sub>A</sub> = -55°C) (I <sub>C</sub> = 150 mA, V <sub>CE</sub> = 10 Vdc) (Note 2) (I <sub>C</sub> = 150 mA, V <sub>CE</sub> = 1.0 Vdc) (Note 2) (I <sub>C</sub> = 500 mA, V <sub>CE</sub> = 10 Vdc) (Note 2)	h <sub>FE</sub>	35 50 75 35 100 50 40	– – – – 300 – –	–
Collector-Emitter Saturation Voltage (Note 2) (I <sub>C</sub> = 150 mA, I <sub>B</sub> = 15 mA) (I <sub>C</sub> = 500 mA, I <sub>B</sub> = 50 mA)	V <sub>CE(sat)</sub>	– –	0.3 1.0	Vdc
Base-Emitter Saturation Voltage (Note 2) (I <sub>C</sub> = 150 mA, I <sub>B</sub> = 15 mA) (I <sub>C</sub> = 500 mA, I <sub>B</sub> = 50 mA)	V <sub>BE(sat)</sub>	0.6 –	1.2 2.0	Vdc

## SMALL-SIGNAL CHARACTERISTICS

Current-Gain - Bandwidth Product (Note 3) (I <sub>C</sub> = 20 mA, V <sub>CE</sub> = 20 Vdc, f = 100 MHz)	f <sub>T</sub>	300	–	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	–	8.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	–	25	pF
Input Impedance (I <sub>C</sub> = 1.0 mA, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz) (I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>ie</sub>	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio (I <sub>C</sub> = 1.0 mA, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz) (I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>re</sub>	– –	8.0 4.0	X 10 <sup>-4</sup>
Small-Signal Current Gain (I <sub>C</sub> = 1.0 mA, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz) (I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>fe</sub>	50 75	300 375	–
Output Admittance (I <sub>C</sub> = 1.0 mA, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz) (I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>oe</sub>	5.0 25	35 200	μmhos
Collector Base Time Constant (I <sub>E</sub> = 20 mA, V <sub>CB</sub> = 20 Vdc, f = 31.8 MHz)	r <sub>b</sub> , C <sub>c</sub>	–	150	ps
Noise Figure (I <sub>C</sub> = 100 μA, V <sub>CE</sub> = 10 Vdc, R <sub>S</sub> = 1.0 kΩ, f = 1.0 kHz)	NF	–	4.0	dB

## SWITCHING CHARACTERISTICS

Delay Time	(V <sub>CC</sub> = 30 Vdc, V <sub>BE(off)</sub> = -0.5 Vdc, I <sub>C</sub> = 150 mA, I <sub>B1</sub> = 15 mA)	t <sub>d</sub>	–	10	ns
Rise Time		t <sub>r</sub>	–	25	
Storage Time	(V <sub>CC</sub> = 30 Vdc, I <sub>C</sub> = 150 mA, I <sub>B1</sub> = I <sub>B2</sub> = 15 mA)	t <sub>s</sub>	–	225	ns
Fall Time		t <sub>f</sub>	–	60	

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

3. f<sub>T</sub> is defined as the frequency at which |h<sub>fe</sub>| extrapolates to unity.

# MBT2222ADW1, NSVBT2222ADW1

## SWITCHING TIME EQUIVALENT TEST CIRCUITS

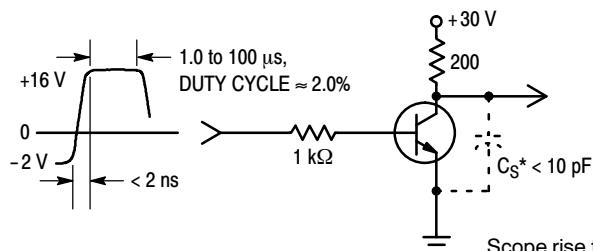


Figure 1. Turn-On Time

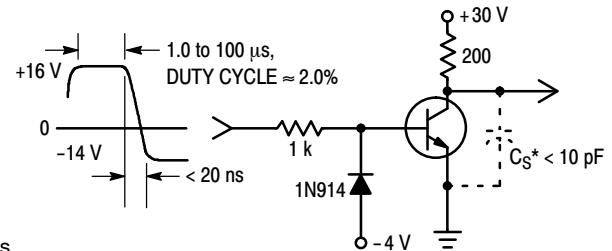


Figure 2. Turn-Off Time

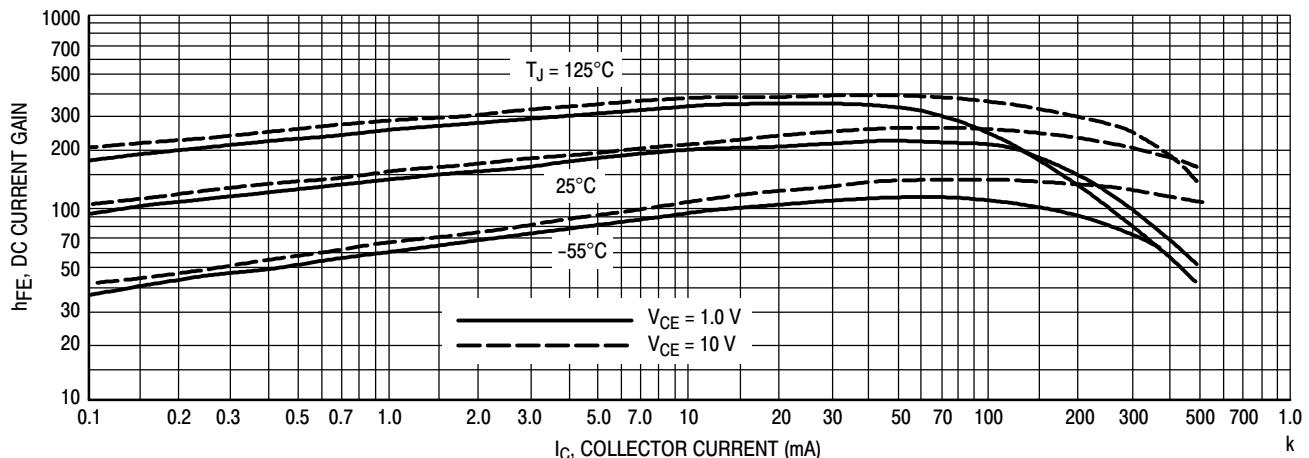


Figure 3. DC Current Gain

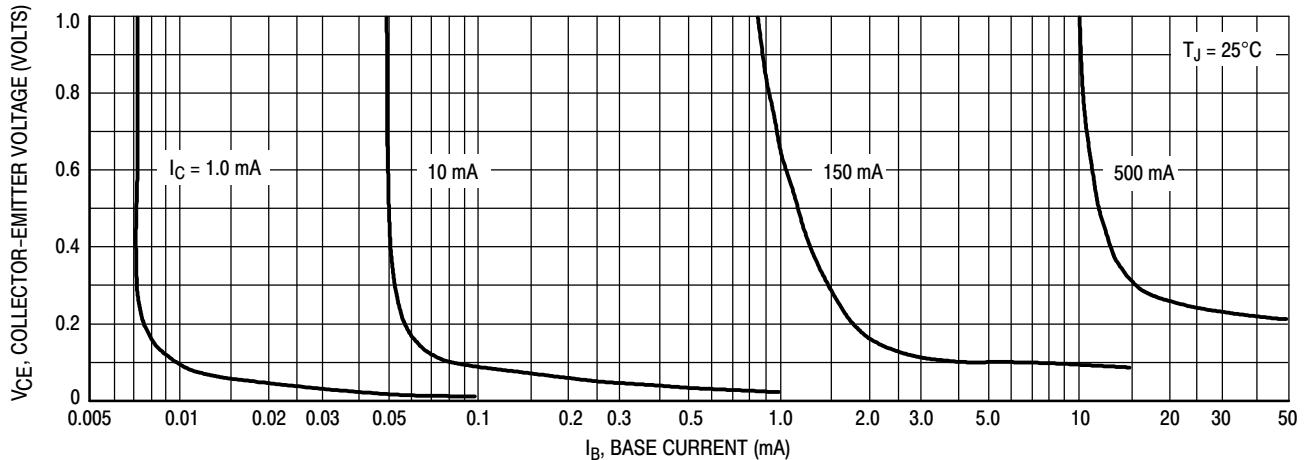


Figure 4. Collector Saturation Region

## MBT2222ADW1, NSVBT2222ADW1

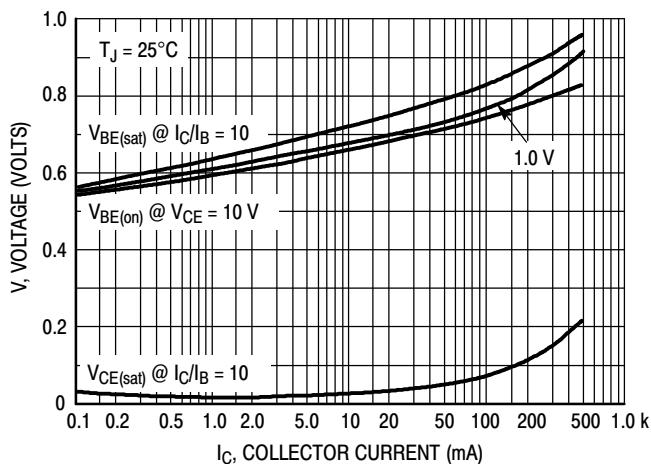


Figure 5. "On" Voltages

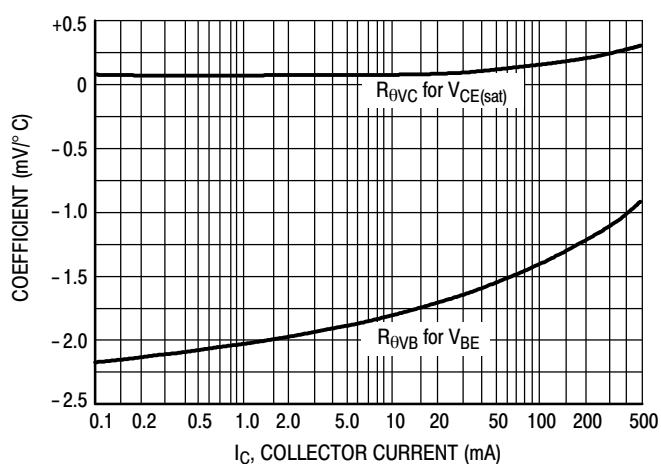


Figure 6. Temperature Coefficients

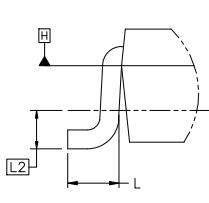
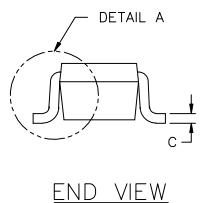
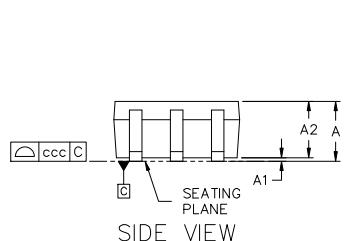
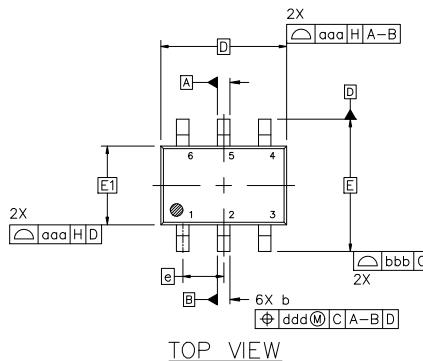


**SC-88 2.00x1.25x0.90, 0.65P**  
**CASE 419B-02**  
**ISSUE Z**

DATE 18 APR 2024

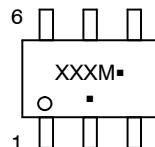
## NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
  2. ALL DIMENSION ARE IN MILLIMETERS.
  3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
  4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
  5. DATUM A AND B ARE DETERMINED AT DATUM H.
  6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
  7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.00	---	0.10
A2	0.70	0.90	1.00
b	0.15	0.20	0.25
c	0.08	0.15	0.22
D	2.00	BSC	
E	2.10	BSC	
E1	1.25	BSC	
e	0.65	BSC	
L	0.26	0.36	0.46
L2	0.15	BSC	
aaa	0.15		
bbb	0.30		
ccc	0.10		
ddd	0.10		

## GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code

XXX = Specific Dev.

■ = Pb-Free Package

**RECOMMENDED MOUNTING FOOTPRINT\***

\* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL. SOI DFRM1D.

(Note: Microdot may be in either location)

\*Date Code orientation and/or position may vary depending upon manufacturing location.

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

#### STYLES ON PAGE 2

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**SC-88 2.00x1.25x0.90, 0.65P**  
CASE 419B-02  
ISSUE Z

DATE 18 APR 2024

STYLE 1: PIN 1. Emitter 2 2. Base 2 3. Collector 1 4. Emitter 1 5. Base 1 6. Collector 2	STYLE 2: Cancelled	STYLE 3: Cancelled	STYLE 4: PIN 1. Cathode 2. Cathode 3. Collector 4. Emitter 5. Base 6. Anode	STYLE 5: PIN 1. Anode 2. Anode 3. Collector 4. Emitter 5. Base 6. Cathode	STYLE 6: PIN 1. Anode 2 2. N/C 3. Cathode 1 4. Anode 1 5. N/C 6. Cathode 2
STYLE 7: PIN 1. Source 2 2. Drain 2 3. Gate 1 4. Source 1 5. Drain 1 6. Gate 2	STYLE 8: Cancelled	STYLE 9: PIN 1. Emitter 2 2. Emitter 1 3. Collector 1 4. Base 1 5. Base 2 6. Collector 2	STYLE 10: PIN 1. Source 2 2. Source 1 3. Collector 1 4. Drain 1 5. Drain 2 6. Gate 2	STYLE 11: PIN 1. Cathode 2 2. Cathode 2 3. Anode 1 4. Cathode 1 5. Cathode 1 6. Anode 2	STYLE 12: PIN 1. Anode 2 2. Anode 2 3. Cathode 1 4. Anode 1 5. Anode 1 6. Cathode 2
STYLE 13: PIN 1. Anode 2. N/C 3. Collector 4. Emitter 5. Base 6. Cathode	STYLE 14: PIN 1. Vref 2. GND 3. GND 4. Iout 5. Ven 6. Vcc	STYLE 15: PIN 1. Anode 1 2. Anode 2 3. Anode 3 4. Cathode 3 5. Cathode 2 6. Cathode 1	STYLE 16: PIN 1. Base 1 2. Emitter 2 3. Collector 2 4. Base 2 5. Emitter 1 6. Collector 1	STYLE 17: PIN 1. Base 1 2. Emitter 1 3. Collector 2 4. Base 2 5. Emitter 2 6. Collector 1	STYLE 18: PIN 1. Vin1 2. Vcc 3. Vout2 4. Vin2 5. Gnd 6. Vout1
STYLE 19: PIN 1. Iout 2. Gnd 3. Gnd 4. Vcc 5. Ven 6. Vref	STYLE 20: PIN 1. Collector 2. Collector 3. Base 4. Emitter 5. Collector 6. Collector	STYLE 21: PIN 1. Anode 1 2. N/C 3. Anode 2 4. Cathode 2 5. N/C 6. Cathode 1	STYLE 22: PIN 1. D1 (l) 2. Gnd 3. D2 (l) 4. D2 (c) 5. Vbus 6. D1 (c)	STYLE 23: PIN 1. Vn 2. Ch1 3. Vp 4. N/C 5. Ch2 6. N/C	STYLE 24: PIN 1. Cathode 2. Anode 3. Cathode 4. Cathode 5. Cathode 6. Cathode
STYLE 25: PIN 1. Base 1 2. Cathode 3. Collector 2 4. Base 2 5. Emitter 6. Collector 1	STYLE 26: PIN 1. Source 1 2. Gate 1 3. Drain 2 4. Source 2 5. Gate 2 6. Drain 1	STYLE 27: PIN 1. Base 2 2. Base 1 3. Collector 1 4. Emitter 1 5. Emitter 2 6. Collector 2	STYLE 28: PIN 1. Drain 2. Drain 3. Gate 4. Source 5. Drain 6. Drain	STYLE 29: PIN 1. Anode 2. Anode 3. Collector 4. Emitter 5. Base/Anode 6. Cathode	STYLE 30: PIN 1. Source 1 2. Drain 2 3. Drain 2 4. Source 2 5. Gate 1 6. Drain 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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